

Silicon Diode

1N5619GP

Fast Switching Rectifier

600V / 1A

DATASHEET

OEM – General Semiconductor

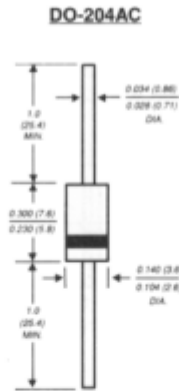
Source: General Semiconductor Databook 1998

1N5615GP THRU 1N5623GP

GLASS PASSIVATED JUNCTION FAST SWITCHING RECTIFIER

Reverse Voltage - 200 to 1000 Volts Forward Current - 1.0 Ampere

PATENTED*



Dimensions in inches and (millimeters)

* Glass-plastic encapsulation technique is covered by Patent No. 3,996,602 and brazed-lead assembly by Patent No. 3,930,306



FEATURES

- ◆ Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- ◆ High temperature metallurgically bonded construction
- ◆ Glass passivated cavity-free junction
- ◆ Capable of meeting environmental standards of MIL-S-19500
- ◆ Fast switching for high efficiency
- ◆ 1.0 Ampere operation at $T_A=55^{\circ}\text{C}$ with no thermal runaway
- ◆ High temperature soldering guaranteed: $350^{\circ}\text{C}/10\text{seconds}$, 0.375" (9.5mm) lead length, 5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: JEDEC DO-204AC molded plastic over glass body
Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight: 0.015 ounce, 0.4 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOLS	1N 5615GP	1N 5617GP	1N 5619GP	1N 5621GP	1N 5623GP	UNITS
* Maximum repetitive peak reverse voltage	VRRM	200	400	600	800	1000	Volts
* Maximum RMS voltage	VRMS	140	280	420	560	700	Volts
* Maximum DC blocking voltage	VDC	200	400	600	800	1000	Amps
* Maximum average forward rectified current 0.375" (9.5mm) lead length at $T_A=55^{\circ}\text{C}$	$I_{(AV)}$	1.0					Amp
* Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	50.0					Amps
Maximum instantaneous forward voltage at 1.0A	V_F	1.2					Volts
Maximum DC reverse current at rated DC blocking voltage	I_R	0.5 25.0					μA
$T_A=25^{\circ}\text{C}$ $T_A=100^{\circ}\text{C}$							
*Maximum reverse recovery time (NOTE 1)	t_{rr}	150	250	300	500		ns
Typical junction capacitance (NOTE 2)	C_J	25.0					pF
Typical thermal resistance (NOTE 3)	$R_{\theta JA}$	45.0					$^{\circ}\text{C}/\text{W}$
* Operating junction and storage temperature range	T_J, T_{STG}	-65 to +175					$^{\circ}\text{C}$

NOTES:

- (1) Reverse recovery test conditions: $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{rr}=0.25\text{A}$
 - (2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts
 - (3) Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted
- * JEDEC registered values

RATINGS AND CHARACTERISTIC CURVES 1N5615GP THRU 1N5623GP

